

**AMENDMENTS TO THE CLAIMS:**

The following listing of claims replaces all prior listings, and all prior versions, of claims in the application.

**LISTING OF CLAIMS:**

1. (Currently amended) A stamper comprising a substrate and a plurality of protrusions having different heights formed on one of the surfaces of said substrate, wherein the protrusions of larger height have a stack structure of at least two layers respectively of different materials, the different materials including silicon oxide and silicon ~~of at least two types of materials.~~

2. (Previously presented) A stamper according to Claim 1, wherein the protrusions of smaller height among said protrusions of different heights have a stack structure with a smaller number of layers than the protrusions of larger height.

3. (Original) A stamper according to Claim 1, wherein the materials of the adjoining ones of the protrusions of larger height have different etching rates for a predetermined etching technique.

4. (Original) A stamper according to Claim 1, wherein the material of said substrate and the materials of said protrusions in contact with said substrate have different etching rates.

5. (Original) A stamper according to Claim 1, wherein the portions of said protrusions at the same height from the surface of said substrate are formed of the same type of material.

6. (Original) A stamper according to Claim 5, wherein the portions of said protrusions in steps of different heights are each formed of a single material.

7. (Original) A stamper fabricated by forming a film of a covering material on the surface of an original stamper described in Claim 1 having a plurality of protrusions of different heights, and removing said original stamper, said stamper having said film of said covering material.

8. (Original) A stamper fabricated by forming a film of a first covering material on the surface of the original stamper according to Claim 1 having protrusions, forming a film of a second covering material on the surface of said film of said first material having the protrusions obtained by removing said original stamper, and removing said film of said first covering material, said stamper having said film of said second covering material.

9. – 11. (Cancelled).

12. (New) A stamper according to Claim 1, wherein said substrate is of silicon, protrusions of smaller height include a layer of silicon oxide adjacent the silicon substrate, and the protrusions of larger height include a layer of silicon oxide adjacent the silicon substrate and a layer of silicon over the layer of silicon oxide.

13. (New) A stamper according to Claim 12, wherein the silicon substrate is a single crystal silicon substrate.

14. (New) A stamper according to Claim 1, wherein the substrate is a silicon substrate, and wherein each of the plurality of protrusions includes a silicon oxide layer adjacent the substrate.

15. (New) A stamper according to Claim 1, wherein said stamper has a structure so as to be used for processing a resist to be a mask that performs a processing for a substrate being processed.